

ABSTRACT OF THE DISCLOSURE

A TFT capable of showing a large gm (large ON-current) and having characteristics comparable to those of Si-MOSFET despite of its relatively simple configuration was fabricated by the steps of coating, for example, a positive photo-resist on an Mo film; subjecting the photo-resist to back light exposure from the glass-substrate side under masking with a bottom gate electrode, to thereby form a resist pattern having the same geometry and being aligned with the bottom gate electrode because exposure light is intercepted by the bottom gate electrode but can travel through the Mo film; and etching the Mo film under masking by the resist pattern to thereby form a top gate electrode in conformity with the geometry of the resist pattern in a self-aligned manner.